

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	2453	(titanium near nitride) near25 (dielectric)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	363	((titanium near nitride) near25 (dielectric)) near25 (titanium near3 silicon near3 nitride)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	31	((((titanium near nitride) near25 (dielectric)) near25 (titanium near3 silicon near3 nitride)) near25 (copper)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	1	((((titanium near nitride) near25 (dielectric)) near25 (titanium near3 silicon near3 nitride)) near25 (cu)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	34	((titanium near nitride) near25 (dielectric)) near25 (titanium near3 nitride)) near25 (cu)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
6	BRS	L6	120	((dielectric or insulat\$3) near25 (titanium near3 nitride)) near25 (cu)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L7	736	((dielectric or insulat\$3) near25 (titanium near3 nitride)) near25 (cu or copper)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
8	BRS	L8	54	((low) near3 (dielectric or insulat\$3) near25 (titanium near3 nitride)) near25 (cu or copper)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	0	((low) near3 (dielectric or insulat\$3) near25 (titanium near3 nitride)) near25 (seed)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
10	BRS	L10	58854	(copper or cu or seed) near35 (titanium near3 nitride or tin)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
11	BRS	L11	385	((copper or cu or seed) near35 (titanium near3 nitride or tin)) near25 (plasma)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
12	BRS	L12	4	((copper or cu or seed) near35 (titanium near3 nitride or tin)) near25 ((plasma) near (pvd or physical))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
13	BRS	L13	2704	((copper or cu or seed) near35 (titanium near3 nitride or tin)) near25 (dielectric or insulat\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
14	BRS	L14	50	((copper or cu or seed) near35 (titanium near3 nitride or tin)) near25 ((k) near (dielectric or insulat\$3))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
15	BRS	L15	0	((gas near25 nitrogen) near35 (titanium near3 nitride or tin)) near25 ((k) near (dielectric or insulat\$3))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
16	BRS	L16	0	((ni near25 nitrogen) near35 (titanium near3 nitride or tin)) near25 ((k) near (dielectric or insulat\$3))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
17	BRS	L17	0	((n near25 nitrogen) near35 (titanium near3 nitride or tin)) near25 ((k) near (dielectric or insulat\$3))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
18	BRS	L18	2	((nitrogen) near35 (titanium near3 nitride or tin)) near25 ((k) near (dielectric or insulat\$3))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
19	BRS	L19	4	(("n.sub.2") near35 (titanium near3 nitride or tin)) near25 ((k) near (dielectric or insulat\$3))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
20	BRS	L20	114	(("n.sub.2") near35 (titanium near3 nitride) or (tin)) near25 ((k) near (dielectric or insulat\$3))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
21	BRS	L21	23	20 and soak\$3	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
22	BRS	L22	179	((titanium near3 nitride) or (tin)) near25 ((k) near (dielectric or insulat\$3))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
23	BRS	L23	24	22 and soak\$3	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
24	BRS	L24	387	((titanium near3 nitride) or (tin)) near25 ((low) near3 (dielectric or insulat\$3))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
25	BRS	L25	35	24 and soak\$3	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
26	BRS	L26	7	((titanium near3 nitride) or (tin)) near25 ((low) near3 (dielectric or insulat\$3))) near35 (nitrogen)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
27	BRS	L27	153	((titanium near3 nitride) or (tin)) near25 ((low) near3 (dielectric or insulat\$3))) and (nitrogen)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
28	BRS	L28	101	((titanium near3 nitride) or (tin)) near25 ((low) near3 (dielectric or insulat\$3))) and ((nitrogen) near35 (gas or silane))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
29	BRS	L29	88	28 and plasma	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
30	BRS	L30	6	29 and (titanium near silicon near nitride)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
31	BRS	L31	15	29 and (tisin)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	U	1	Document ID	Title
1			US 20050084619 A1	Method to deposit an impermeable film on porous low-k dielectric film
2			US 20040197492 A1	CVD TiSiN barrier for copper integration
3			US 20040149686 A1	Method to deposit an impermeable film on porous low-k dielectric film
4			US 20040069410 A1	Cluster tool for E-beam treated films
5			US 20030232495 A1	Methods and apparatus for E-beam treatment used to fabricate integrated circuit devices
6			US 20030214043 A1	Semiconductor device
7			US 20030119211 A1	METHOD OF PATTERNING A FERAM CAPACITOR WITH A SIDEWALL DURING BOTTOM ELECTRODE ETCH
8			US 20030059720 A1	Masking methods and etching sequences for patterning electrodes of high density RAM capacitors
9			US 20020072223 A1	Method of enhancing adhesion of a conductive barrier layer to an underlying conductive plug and contact for ferroelectric applications

	U	1	Document ID	Title
10			US 20010030169 A1	Method of etching organic film and method of producing element
11			US 6838772 B2	Semiconductor device
12			US 6635498 B2	Method of patterning a FeRAM capacitor with a sidewall during bottom electrode etch
13			US 6576546 B2	Method of enhancing adhesion of a conductive barrier layer to an underlying conductive plug and contact for ferroelectric applications

	U	1	Document ID	Title
14			US 6548343 B1	Method of fabricating a ferroelectric memory cell
15			US 6492222 B1	Method of dry etching PZT capacitor stack to form high-density ferroelectric memory devices